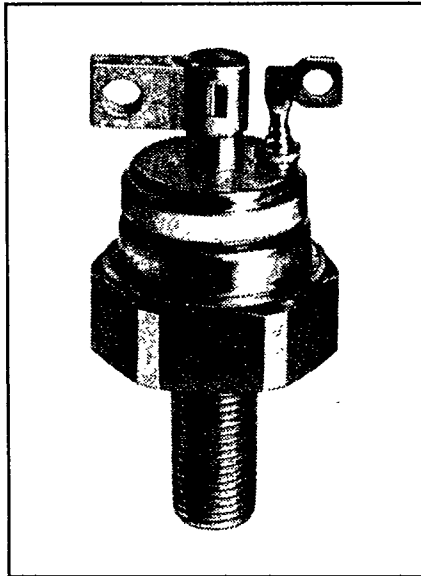
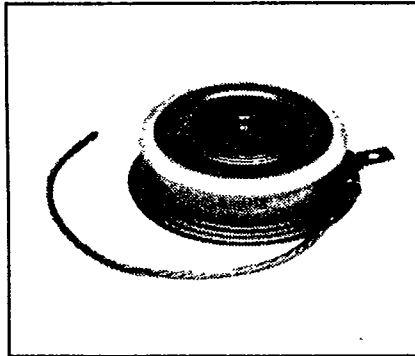


POWEREX

Powerex, Inc., Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272

D60T/D62T___40**D60T/D62T___50****D60T/D62T___60**

T-33-15

NPN**Power Switching Transistors****40-50-60 Amperes****400-500 Volts****D60T___40/50/60****NPN Power Switching Transistors**
40-50-60 Amperes/400-500 Volts**D62T___40/50/60****NPN Power Switching Transistors**
40-50-60 Amperes/400-500 Volts**Features:**

- ☐ Triple Diffused Design
- ☐ Compression Bonded Construction/No Solder
- ☐ Double Sided Cooling on D62T
- ☐ Fast Switching
- ☐ 100 kHz Operation
- ☐ 200 Amperes Peak

Applications:

- ☐ High Frequency Inverters
- ☐ Motor Controls
- ☐ Switching Regulators
- ☐ VLF Transmitters
- ☐ Induction Heating
- ☐ Power Supplies

Ordering Information

Example: Select the complete ten digit part number you desire from the table—i.e. a D62T454010 describes a Disc Package Transistor rated at 450 Volts, 40 Amperes, and a gain of 10 at rated current (40 Amperes). D60T454010 is the same transistor in a stud package.

Type	V _{CEQ(SUS)} Volts (×10)	Current Rating Amperes	Gain
D60T	40	40	10
D62T	45	50	
	50	60	

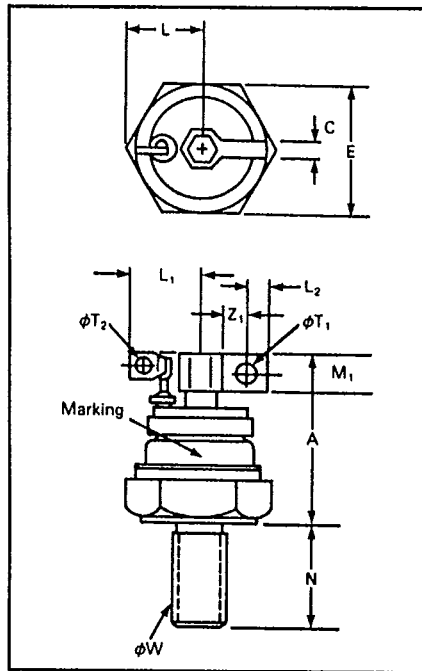
POWEREX

Powerex, Inc., Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272

D60T/D62T___40, D60T/D62T___50, D60T/D62T___60

NPN Power Switching Transistors

40-50-60 Amperes/400-500 Volts



D60T___40/50/60, 400-500 Volts
Outline Drawing

Dimension	Inches		Millimeters	
	Min.	Max.	Min.	Max.
A		1.80		45.72
C	.160	.180	4.06	4.57
E	1.212	1.252	30.78	31.75
L		.812		20.62
L ₁		.64		16.26
L ₂	.155		3.94	
M ₁	.350	.450	8.88	11.42
N	1.040	1.077	24.89	27.69
ϕT_1	.193	.203	4.90	5.16
ϕT_2	.145	.160	3.68	4.06
Z ₁	.22		5.59	
ϕW	1/2-20 UNF 3A			

Creep and Strike Distance:

D60T—17 in. min. (4.3mm).

(In accordance with NEMA standards.)

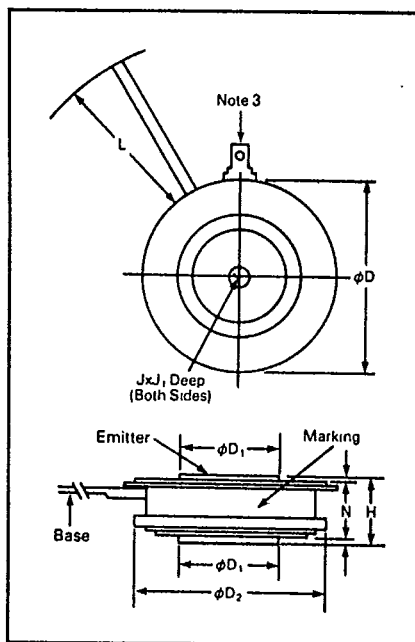
Finish—Nickel Plate.

Approx. Weight—4.9 oz. (140 g).

1. Complete threads to extend to within 2½ threads of seating plane.

2. Angular orientation of terminals is undefined.

3. Pitch diameter of 1/2-20 UNF 3A (COATED) threads (ASA B1.1-1960).



D62T___40/50/60, 400-500 Volts
Outline Drawing

Dimension	Inches		Millimeters	
	Min.	Max.	Min.	Max.
ϕD	1.610	1.650	40.89	41.91
ϕD_1	.745	.755	18.92	19.18
ϕD_2	1.420	1.460	36.07	37.08
H	.500	.560	12.70	14.22
ϕJ	.135	.145	3.43	3.68
J ₁	.072	.082	1.83	2.08
L	4.000		101.6	
N	.030		.76	

Creep Distance—.34 in. min. (8.64mm)

Strike Distance—.52 in. min. (13.21mm)

(In accordance with NEMA standards.)

Finish—Nickel Plate.

Approx. Weight—2.1 oz. (60g).

1. Dimension "H" is a clamped dimension.

2. Base Lead is No. 14 uninsulated flexible stranded wires.

3. Emitter tab for 3/16 inch fast-on terminal.



Powerex, Inc., Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272

D60T/D62T___40, D60T/D62T___50, D60T/D62T___60
NPN Power Switching Transistors
40-50-60 Amperes/400-500 Volts

D60T Maximum Ratings

Characteristics	Symbol	D60T___40/50/60			Units
Operating and Storage Temperature	T_J/T_{STG}	- 65 to 200			$^{\circ}\text{C}$
Emitter Base Voltage	V_{EBO}	7			Volts
Peak Collector Current	$I_C \text{ Peak}$	200			Amperes
Continuous Collector Current ^①	$I_C \text{ Cont.}$	—			Amperes
Continuous Base Current	I_B	20			Amperes
Linear Power Derating Factor from $T_C = 25^{\circ}\text{C}$ to $T_C = 175^{\circ}\text{C}$	—	5.88			$\text{W}/^{\circ}\text{C}$
Thermal Resistance Case to Sink, Lubricated	$R_{\theta CS}$	0.12			$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.17			$^{\circ}\text{C}/\text{W}$
Power Dissipation $T_C = 25^{\circ}\text{C}$	P_T	885			Watts
Power Dissipation $T_C = 75^{\circ}\text{C}$	P_T	590			Watts
Mounting Torque Non-Lubricated Threads		130			in.-lb.
Mounting Torque Non-Lubricated Threads		14.46			N-M
		D60T4040 D60T4050 D60T4060	D60T4540 D60T4550 D60T4560	D60T5040 D60T5050 D60T5060	
Collector Emitter Sustaining Voltage ^②	$V_{CEQ(SUS)}$	400	450	500	Volts
Collector Base Voltage	V_{CBO}	450	500	550	Volts
Collector Emitter Voltage $V_{BE} = -1.5\text{V}$	V_{CEV}	450	500	550	Volts

① Collector current limited by base current. Base current must not exceed 20 Amperes, RMS, 28 Amperes square wave 50% duty cycle or 40 Amperes peak $\frac{1}{2}$ sine wave.

② $V_{CEQ(SUS)}$ must not be measured on a curve tracer.



Powerex, Inc., Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272

D60T/D62T___40, D60T/D62T___50, D60T/D62T___60

NPN Power Switching Transistors

40-50-60 Amperes/400-500 Volts

D62T Maximum Ratings

Characteristics	Symbol	D62T___40/50/60			Units
Operating and Storage Temperature	T_J/T_{STG}	-65 to 200			°C
Emitter Base Voltage	V_{EBO}	7			Volts
Peak Collector Current	I_C Peak	200			Amperes
Continuous Collector Current ^①	I_C Cont.	—			Amperes
Continuous Base Current	I_B	20			Amperes
Linear Power Derating Factor from $T_C=25^\circ\text{C}$ to $T_C=175^\circ\text{C}$	—	11.11			W/°C
Thermal Impedance, Double Sided Cooling Case to Sink, Lubricated	$R_{\theta CS}$	0.05			°C/W
Thermal Impedance, Junction to Case	$R_{\theta JC}$	0.09			°C/W
Power Dissipation $T_C=25^\circ\text{C}$	P_T	1650			Watts
Power Dissipation $T_C=75^\circ\text{C}$	P_T	1100			Watts
Mounting Force		900			lb.
Mounting Force		4.05			kN
		D62T4040 D62T4050 D62T4060	D62T4540 D62T4550 D62T4560	D62T5040 D62T5050 D62T5060	
Collector Emitter Sustaining Voltage ^②	$V_{CEQ(SUS)}$	400	450	500	Volts
Collector Base Voltage	V_{CBO}	450	500	550	Volts
Collector Emitter Voltage $V_{BE} = -1.5\text{V}$	V_{CEV}	450	500	550	Volts

① Collector current limited by base current. Base current must not exceed 20 Amperes, RMS, 28 Amperes square wave 50% duty cycle or 40 Amperes peak ½ sine wave.

② $V_{CEQ(SUS)}$ must not be measured on a curve tracer.



Powerex, Inc., Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272

D60T/D62T___40, D60T/D62T___50, D60T/D62T___60

NPN Power Switching Transistors

40-50-60 Amperes/400-500 Volts

Electrical and Mechanical Characteristics $T_c, T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	D60T/D62T___40/50/60			Units
			Min.	Typ.	Max.	
Collector Cutoff Current (Base Emitter Reverse Biased)	I_{CEV}	At Rated V_{CEV} $V_{BE(OFF)} = -1.5\text{V}$	—	0.1	1	mA
Collector Cutoff Current (Base Emitter Reverse Biased)	I_{CEV}	At Rated V_{CEV} $V_{BE(OFF)} = -1.5\text{V}, T_j = 150^\circ\text{C}$	—	0.8	3	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 7\text{V}$	—	2	30	mA
Output Capacitance	C_{OB}	$f_{TEST} = 1\text{ MHz}, V_{CB} = 10\text{V}$	—	2500	—	μf
Gain-Bandwidth	f_T	$f_{TEST} = 1\text{ MHz}, I_C = 5\text{A}, V_{CE} = 10\text{V}$	7	10	—	MHz
D60T/D62T___40						
DC Current Gain	h_{FE}	$I_C = 40\text{A}, V_{CE} = 2.5\text{V}$	10	—	—	—
		$I_C = 40\text{A}, V_{CE} = 5\text{V}$	10	—	—	—
		$I_C = 80\text{A}, V_{CE} = 2.5\text{V}$	—	5	—	—
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 40\text{A}, I_B = 6\text{A}$	—	—	1.25	Volts
		$I_C = 40\text{A}, I_B = 4.8\text{A}$	—	—	1.25	Volts
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = 40\text{A}, I_B = 6\text{A}$	—	—	1.50	Volts
		$I_C = 40\text{A}, I_B = 4.8\text{A}$	—	—	1.40	Volts
Resistive Load Switch Times	Turn-On Delay	t_d $V_{CC} = 250\text{V}, I_C = 40\text{A}$	—	—	110	ns
	Rise Time	t_r $I_{B1} = -I_{B2} = 6\text{A}$	—	0.7	1.0	μs
	Storage Time	t_s $t_p = 50\text{ }\mu\text{s}$	—	1.25	3.0	μs
	Fall Time	t_f Duty Cycle < 2%	—	0.3	0.5	μs
D60T/D62T___50						
DC Current Gain	h_{FE}	$I_C = 50\text{A}, V_{CE} = 2.5\text{V}$	10	—	—	—
		$I_C = 100\text{A}, V_{CE} = 2.5\text{V}$	—	5	—	—
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 50\text{A}, I_B = 6\text{A}$	—	—	1.25	Volts
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = 50\text{A}, I_B = 6\text{A}$	—	—	1.50	Volts
Resistive Load Switch Times	Turn-On Delay	t_d $V_{CC} = 250\text{V}, I_C = 50\text{A}$	—	—	120	ns
	Rise Time	t_r $I_{B1} = -I_{B2} = 7.5\text{A}$	—	0.8	1.10	μs
	Storage Time	t_s $t_p = 50\text{ }\mu\text{s}$	—	1.75	3.0	μs
	Fall Time	t_f Duty Cycle < 2%	—	0.35	0.5	μs
D60T/D62T___60						
DC Current Gain	h_{FE}	$I_C = 60\text{A}, V_{CE} = 2.5\text{V}$	10	—	—	—
		$I_C = 120\text{A}, V_{CE} = 2.5\text{V}$	—	5	—	—
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 60\text{A}, I_B = 6\text{A}$	—	—	1.25	Volts
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = 60\text{A}, I_B = 6\text{A}$	—	—	1.60	Volts
Resistive Load Switch Times	Turn-On Delay	t_d $V_{CC} = 250\text{V}, I_C = 60\text{A}$	—	—	150	ns
	Rise Time	t_r $I_{B1} = -I_{B2} = 9\text{A}$	—	0.85	1.20	μs
	Storage Time	t_s $t_p = 50\text{ }\mu\text{s}$	—	2.0	3.0	μs
	Fall Time	t_f Duty Cycle < 2%	—	0.35	0.5	μs



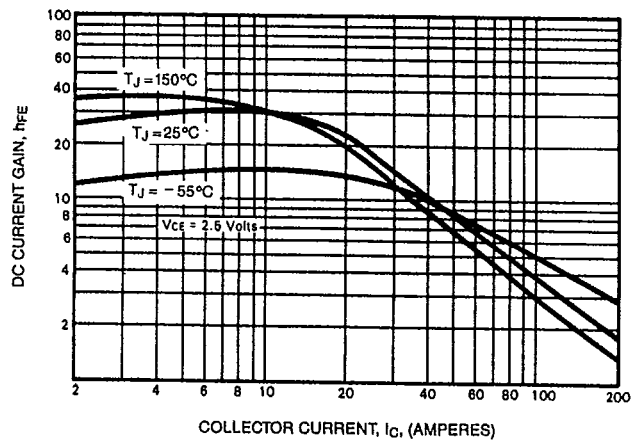
Powerex, Inc., Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272

D60T/D62T___40, D60T/D62T___50, D60T/D62T___60

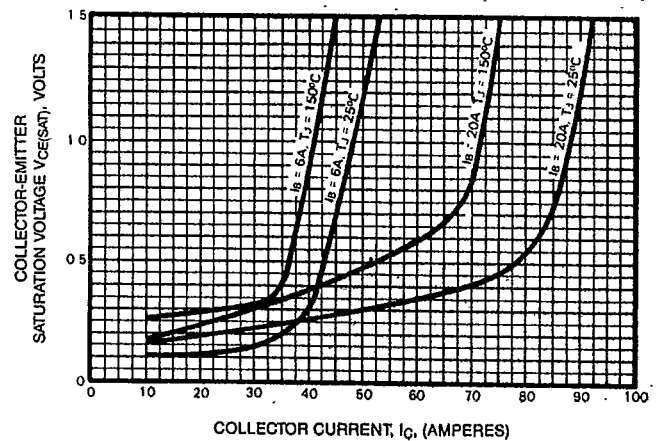
NPN Power Switching Transistors

40-50-60 Amperes/400-500 Volts

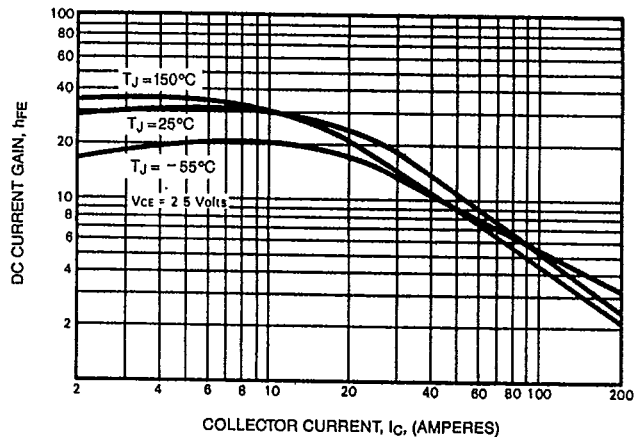
DC CURRENT GAIN (TYPICAL)
D60T/D62T___40



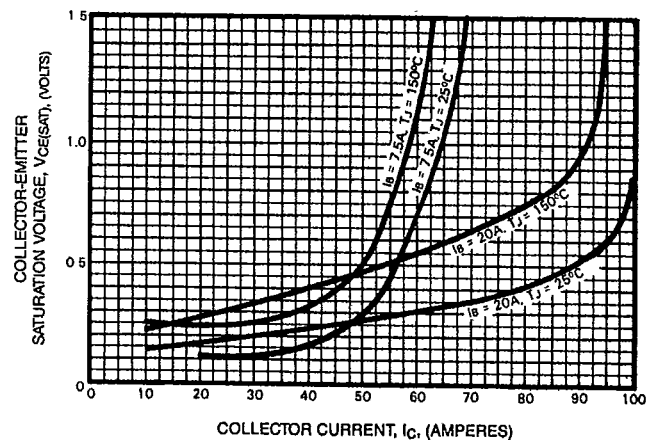
SATURATION VOLTAGE (TYPICAL)
D60T/D62T___40



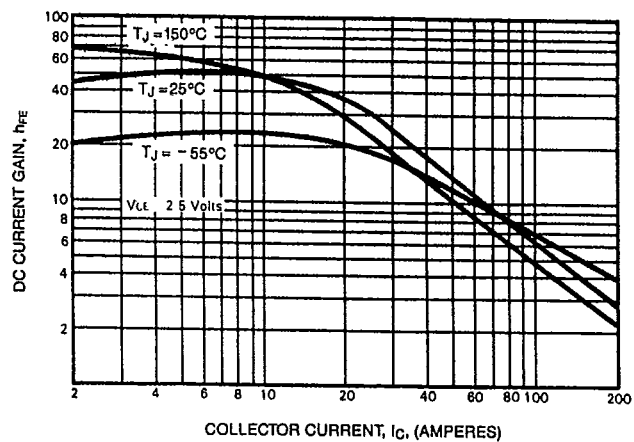
DC CURRENT GAIN (TYPICAL)
D60T/D62T___50



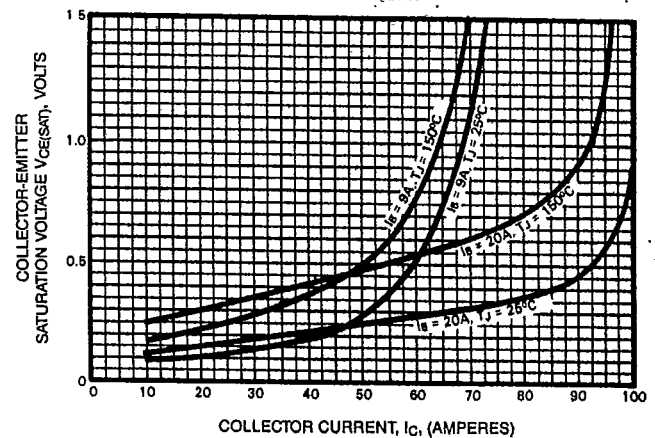
SATURATION VOLTAGE (TYPICAL)
D60T/D62T___50



DC CURRENT GAIN (TYPICAL)
D60T/D62T___60



SATURATION VOLTAGE (TYPICAL)
D60T/D62T___60



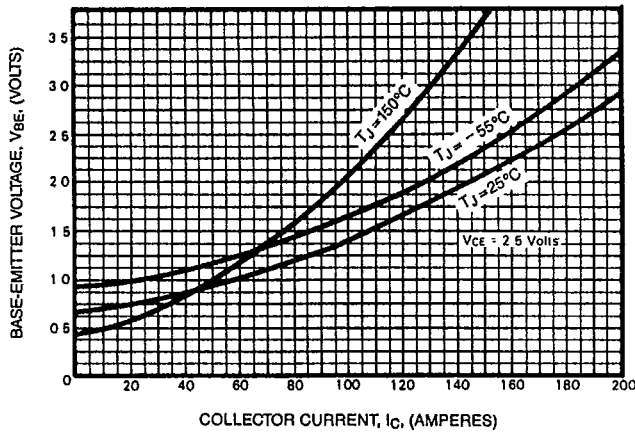
POWEREX

T-33-15

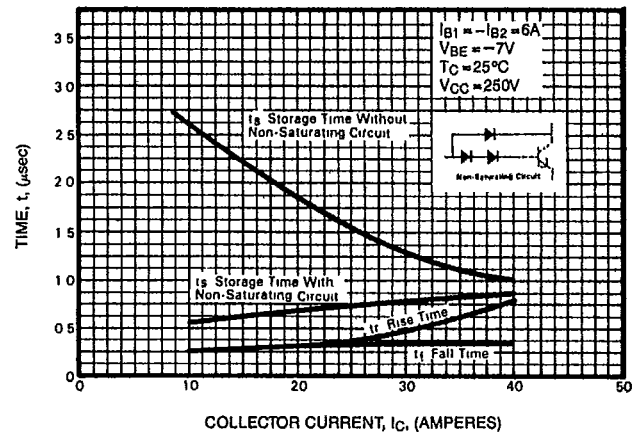
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D60T/D62T___40, D60T/D62T___50, D60T/D62T___60
NPN Power Switching Transistors
40-50-60 Amperes/400-500 Volts

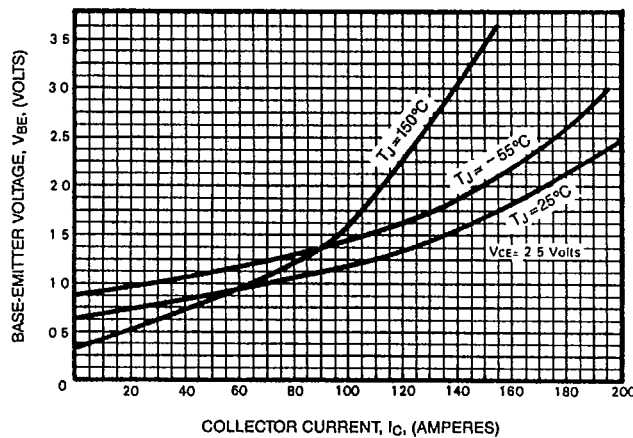
TRANSFER CHARACTERISTICS (TYPICAL)
D60T/D62T___40



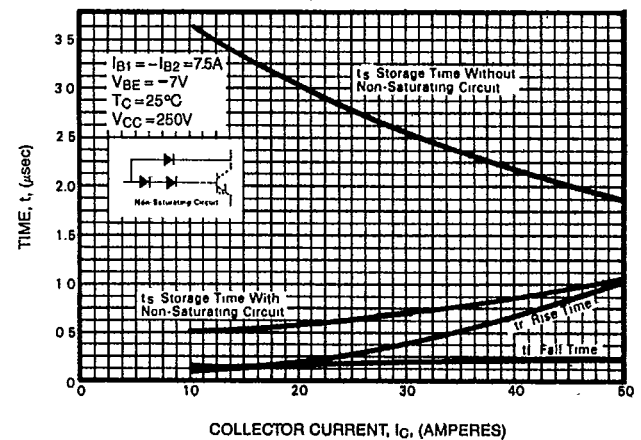
RESISTIVE SWITCHING (TYPICAL)
D60T/D62T___40



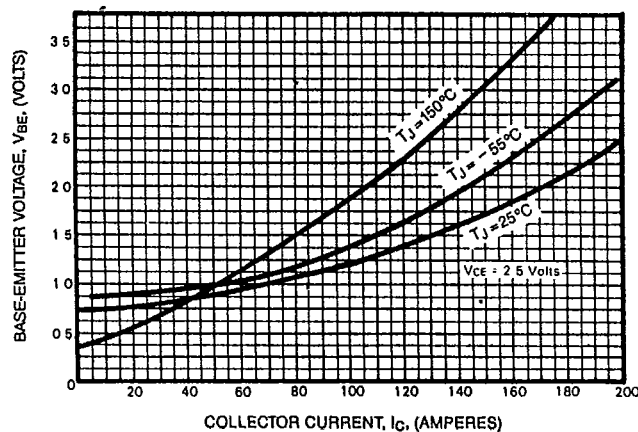
TRANSFER CHARACTERISTICS (TYPICAL)
D60T/D62T___50



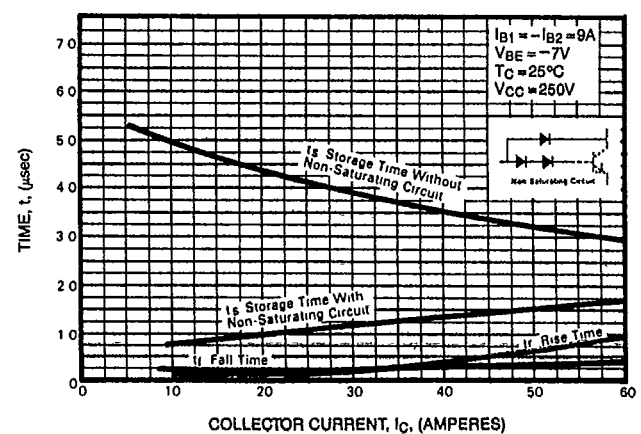
RESISTIVE SWITCHING (TYPICAL)
D60T/D62T___50



TRANSFER CHARACTERISTICS (TYPICAL)
D60T/D62T___60



RESISTIVE SWITCHING (TYPICAL)
D60T/D62T___60

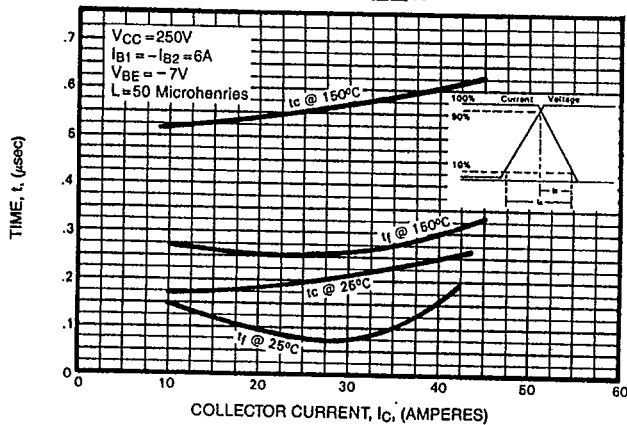




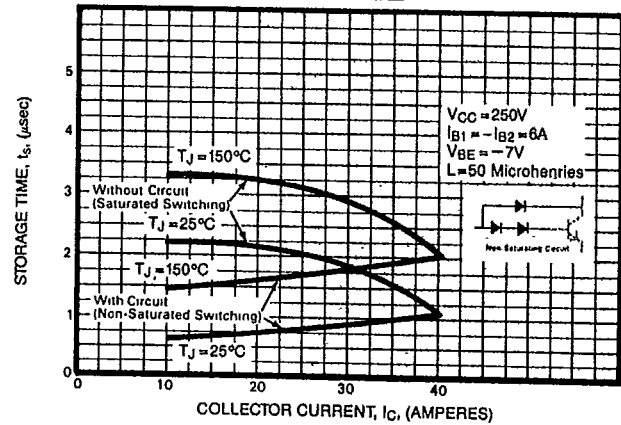
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D60T/D62T___40, D60T/D62T___50, D60T/D62T___60
NPN Power Switching Transistors
40-50-60 Amperes/400-500 Volts

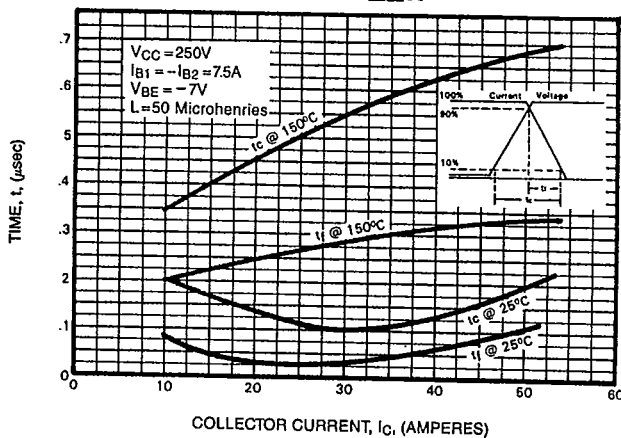
TURN-OFF TIME FOR CLAMPED
INDUCTIVE SWITCHING (TYPICAL)
D60T/D62T___40



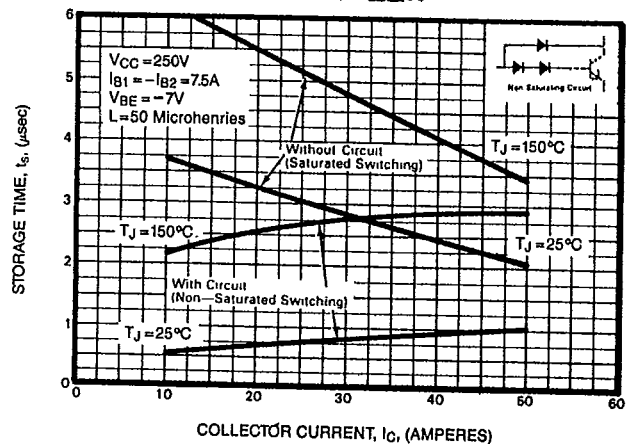
STORAGE TIME FOR
CLAMPED INDUCTIVE SWITCHING (TYPICAL)
D60T/D62T___40



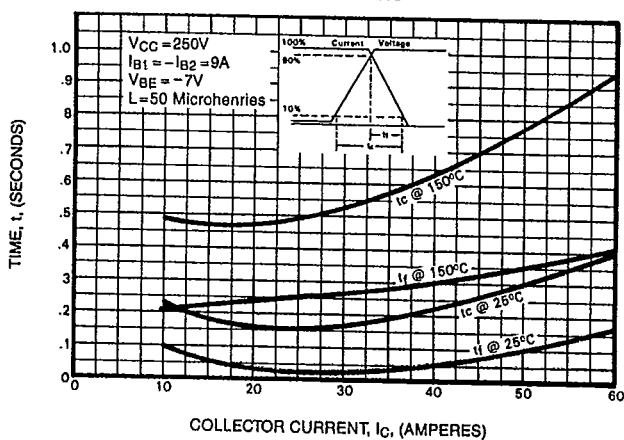
TURN-OFF TIME FOR CLAMPED
INDUCTIVE SWITCHING (TYPICAL)
D60T/D62T___50



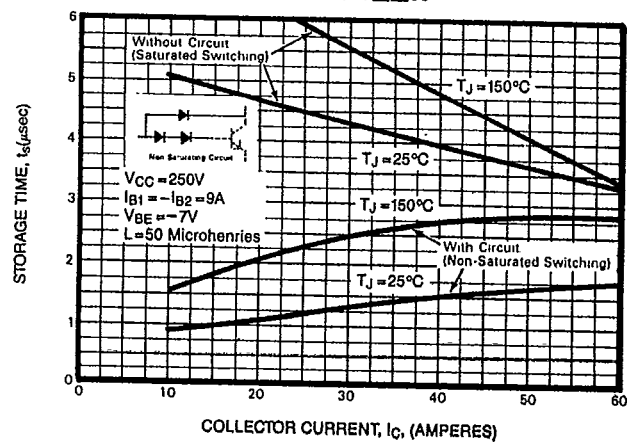
STORAGE TIME FOR
CLAMPED INDUCTIVE SWITCHING (TYPICAL)
D60T/D62T___50



TURN-OFF TIME FOR CLAMPED
INDUCTIVE SWITCHING (TYPICAL)
D60T/D62T___60



STORAGE TIME FOR
CLAMPED INDUCTIVE SWITCHING (TYPICAL)
D60T/D62T___60

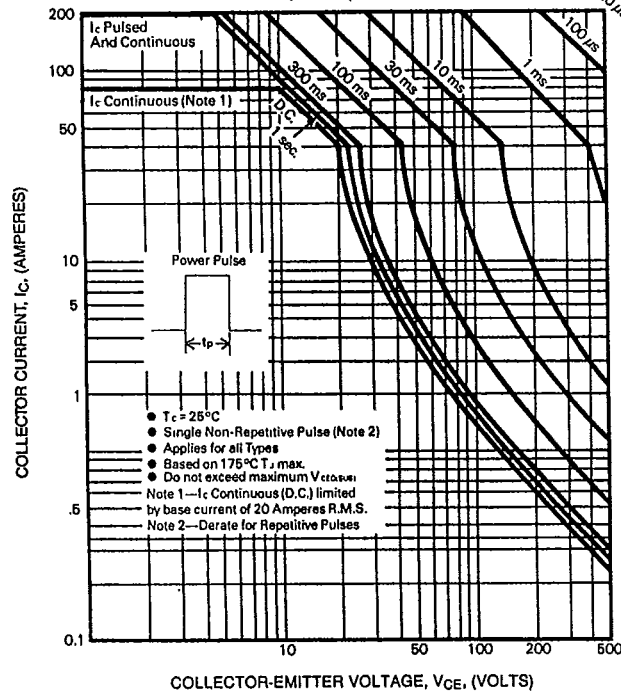




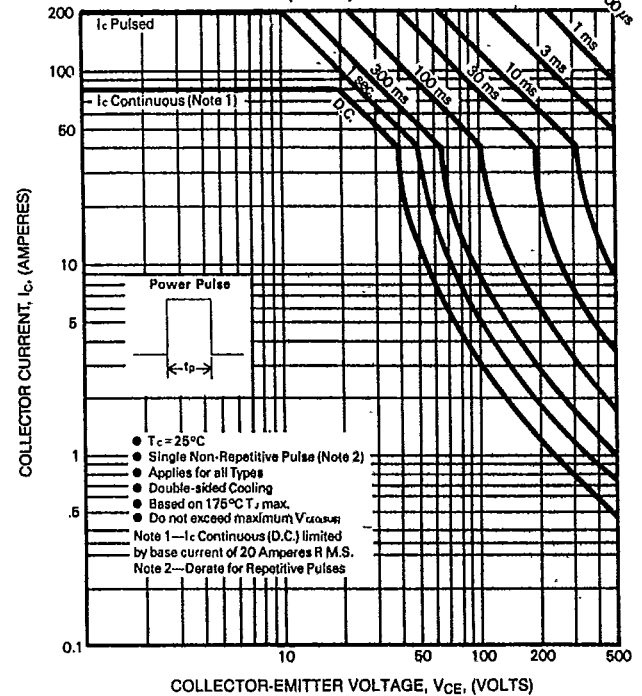
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D60T/D62T___40, D60T/D62T___50, D60T/D62T___60
NPN Power Switching Transistors
40-50-60 Amperes/400-500 Volts

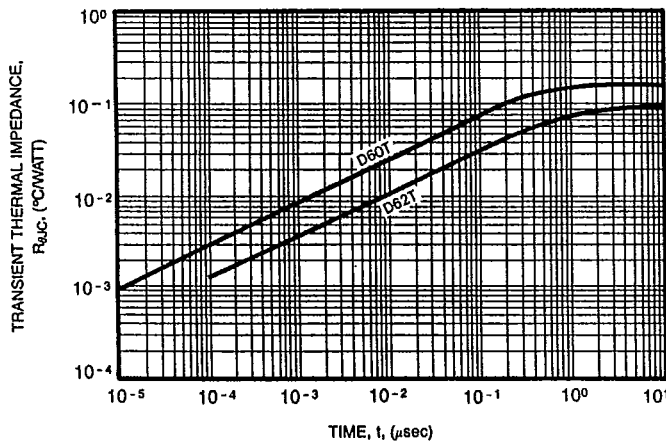
FORWARD BIAS SAFE OPERATING AREA
(S.O.A.) D60T



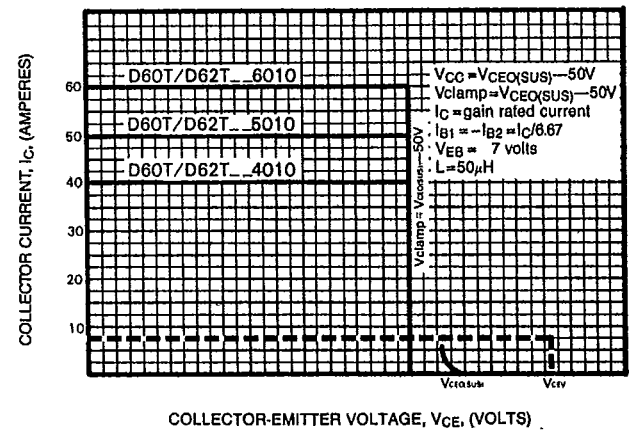
FORWARD BIAS SAFE OPERATING AREA
(S.O.A.) D62T



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
D60T/D62T



REVERSE BIAS SAFE OPERATING AREA
(R.B.S.O.A.) D60T/D62T

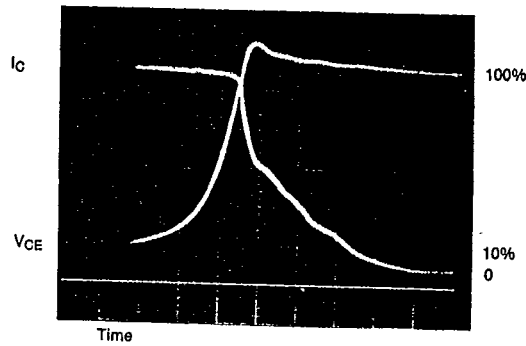




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D60T/D62T___40, D60T/D62T___50, D60T/D62T___60
NPN Power Switching Transistors
40-50-60 Amperes/400-500 Volts

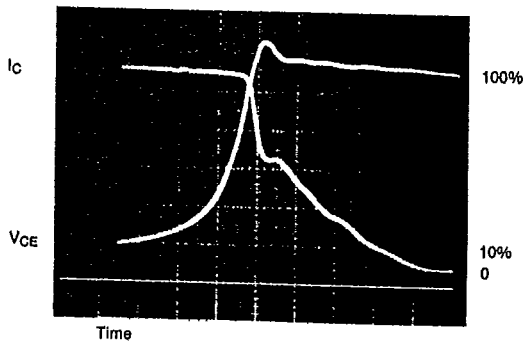
Typical Turn-Off Waveforms for Clamped Inductive Switching*



D60T___40

D62T___40

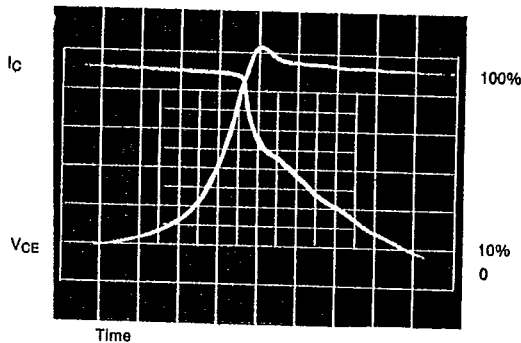
$V_{CE} = 250V, 50V/cm$
 $I_C = 40A$, scale not calibrated
 $I_{B1} = -I_{B2} = 6A, V_{EB} = 7V$
Time = 100 ns/cm
 $T = 150^\circ C$



D60T___50

D62T___50

$V_{CE} = 250V, 50V/cm$
 $I_C = 50A, 10A/cm$
 $I_{B1} = -I_{B2} = 7.5A, V_{EB} = 7V$
Time = 100 ns/cm
 $T = 150^\circ C$



D60T___60

D62T___60

$V_{CE} = 250V, 50V/cm$
 $I_C = 60A$, scale not calibrated
 $I_{B1} = -I_{B2} = 9A, V_{EB} = 7V$
Time = 100 ns/cm
 $T = 150^\circ C$

*Shown above are actual photographs taken during 150°C Inductive switching measurements